

L Number	Hits	Search Text	DB	Time stamp
1	2	("6168991").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 13:01
2	2	("6211005").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:08
3	0	("adhesion near3 tungsten near3 (indium oxide or ito)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:08
4	41	adhesion near3 tungsten near3 (indium oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:09
5	0	adhesion near3 tungsten near3 (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:10
6	0	adhesion near6 tungsten near6 (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:10
7	0	adhesi\$2 near6 tungsten near6 (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:16
8	0	tungsten near3 (plug or contact) near6 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:17
9	2	tungsten near3 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:44
10	2	tungsten near6 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:45
11	2	tungsten near12 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:45
12	494	tungsten near12 (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:46
13	1	tungsten near12 (indium adj oxide or ito) near12 (adhere or adhesion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:47
14	1	tungsten near12 (indium adj oxide or ito) near12 (adhere or adhesion or adhesive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:03

15	1	(w or tungsten) near12 (indium adj oxide or ito) near12 (adhere or adhesion or adhesive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:23
16	21	(w or tungsten) near12 (prevent or preventing) near12 oxidation near12 (contact or plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:36
17	1	(prevent or preventing) near12 oxidation near12 indium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:49
18	7	(tantalum adj nitride or tan) near12 (tungsten or w) near12 (indium adj oxide or ito or indium adj tin adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:53
19	530	(tantalum adj nitride or tan) near12 (tungsten or w) near12 (barrier or passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:53
20	53	(tantalum adj nitride or tan) near3 (tungsten or w) near3 (barrier or passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:54
21	5	(tantalum adj nitride or tan) near3 (tungsten or w) near3 (barrier or passivation).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 16:58
22	135	(tantalum adj nitride or tan) near3 (tungsten or w).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 17:18
23	8	(tantalum adj nitride or tan) near3 (tungsten or w).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 17:26
24	277	(tantalum adj nitride or tan) near3 (tungsten or w) near12 barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 17:27
25	18	(tantalum adj nitride or tan) near3 (tungsten or w) near12 barrier.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 19:16
26	0	(tantalum adj nitride or tan) near3 (indium adj2 oxide or ito) near12 barrier.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 18:08
27	2	("6265260").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 19:17
28	2	("6168991").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 19:39

29	0	("oxidation adj potential near12 (tungsten or W)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 19:39
30	55	oxidation adj potential near12 (tungsten or W)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 19:40
-	6085	((257/68) or (257/71) or (257/296) or (257/300) or (257/306) or (257/308) or (257/309) or (257/310) or (257/311) or (257/761) or (257/763) or (361/303) or (361/305) or (361/306.1) or (361/306.3) or (361/311)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 12:59
-	23	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and tantalum adj nitride and tungsten and substrate 6285072.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:46
-	0		JPO; DERWENT	2001/08/22 18:20
-	3	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/22 20:49
-	2	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate and tantalum adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:49
-	0	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and tantalum adj nitride and tungsten and substrate	EPO; JPO; IBM_TDB	2001/08/23 08:47
-	8	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate and tantalum adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:48
-	0	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate and tantalum adj nitride	EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:48

-	2	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and substrate and tantalum adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:50
-	0	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and substrate and tantalum adj nitride	EPO; JPO; IBM_TDB	2001/08/23 08:50
-	0	semiconductor and (capacitor or dram) and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tantalum adj nitride	EPO; JPO; IBM_TDB	2001/08/23 08:51
-	0	(tantalum adj nitride with work adj function) and semiconductor and dram and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 10:38
-	1	(tantalum adj nitride with work adj function) and semiconductor and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 10:40
-	12	(tantalum adj nitride with work adj function) and (257/\$5.ccls. or 438/\$5.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 10:41
-	3	4663559.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:16
-	0	barrier with tantal\$2 adj nitride with ev	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:47
-	522	barrier with tantal\$2 adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:47
-	141	diffusion adj barrier with tantal\$2 adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:47
-	0	diffusion adj barrier with tantal\$2 adj nitride with work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:48
-	0	diffusion adj barrier with tantal\$2 adj nitride same work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:48
-	0	(diffusion adj barrier with tantal\$2 adj nitride) same work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:48

-	0	(diffusion adj barrier with tant\$4 adj nitride) same work adj function	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:49
-	1	(diffusion adj barrier with tant\$4 adj nitride) and (tant\$4 adj nitride same work adj function)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:06
-	0	diffusion adj barrier with tant\$4 adj nitride with indium adj oxide	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:06
-	3	(diffusion adj barrier with tant\$4 adj nitride) and (semiconductor.ti,ab. and capacitor.ti,ab.)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:38
-	1	(leakage adj current with tant\$4 adj nitride) and (semiconductor.ti,ab. and capacitor.ti,ab.)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:42
-	17	(barrier with tant\$4 adj nitride) and (semiconductor.ti,ab. and capacitor.ti,ab.)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:52
-	2	jp-10320569\$-\$.did.	JPO; DERWENT	2001/08/23 19:32
-	626	effective adj refractive adj index	JPO; DERWENT	2001/08/23 19:33
-	99	effective adj refractive adj index near10 mode	JPO; DERWENT	2001/08/23 19:33
-	61	effective adj refractive adj index near4 mode	JPO; DERWENT	2001/08/23 19:34
-	310	effective adj refractive adj index near4 mode	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2001/08/23 19:34
-	26	effective adj refractive adj index with waveguide adj mode	USPÄT; US-PGPUB; EPO; DERWENT; IBM_TDB	2001/08/23 19:34
-	6349	((257/68) or (257/71) or (257/296) or (257/300) or (257/306) or (257/308) or (257/309) or (257/310) or (257/311) or (257/761) or (257/763) or (361/303) or (361/305) or (361/306.1) or (361/306.3) or (361/311)).CCLS.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 13:36
-	0	("L4 and (indium adj2 oxide near10 (storage or first or second or cell) adj2 electrode))").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 13:39
-	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj2 oxide near10 (storage or first or second or cell) adj2 electrode)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 13:43

-	6	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj2 oxide same (storage or first or second or cell) adj2 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 14:03
-	9	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj oxide same electrode) and capacitor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 14:51
-	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (purpose same indium adj oxide same electrode) and capacitor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:17
-	2	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (purpose same indium adj oxide same electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:06
-	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near4 (plug or via)) and (electrode same indium adj oxide) and (dielectric near10 (tantalum adj oxide or tantalum adj pentoxide)) and (capacitor or dram)ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:10
-	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near4 (plug or via)) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near10 (tantalum adj oxide or tantalum adj pentoxide)) and (capacitor or dram or electrode).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:13
-	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near4 (plug or via)) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near10 (tantalum adj oxide or tantalum adj pentoxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:14

-	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near12 (plug or via)) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:15
-	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:36
-	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide)) and (dram or capacitor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:17
-	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide)) and (dram or capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:17
-	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((reductive or prtoection or protecting or protect) same tantalum adj nitride same indium adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:37
-	0	(tantalum adj nitride near12 indium adj oxide) same (protect or protection or protecting or protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:39
-	0	(tantalum adj nitride same indium adj oxide) same (protect or protection or protecting or protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:40
-	33	tantalum adj nitride same indium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:40

-	0	tantalum adj nitride same indium adj oxide same (protect or cover or reduct\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:41
-	1815	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near12 indium oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:42
-	1815	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near4 indium oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
-	1815	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near2 indium oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
-	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near2 indium adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
-	2	hdp near3 silicon adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 10:16